

Nanodiamond photocathodes for MPGD-based single photon detectors

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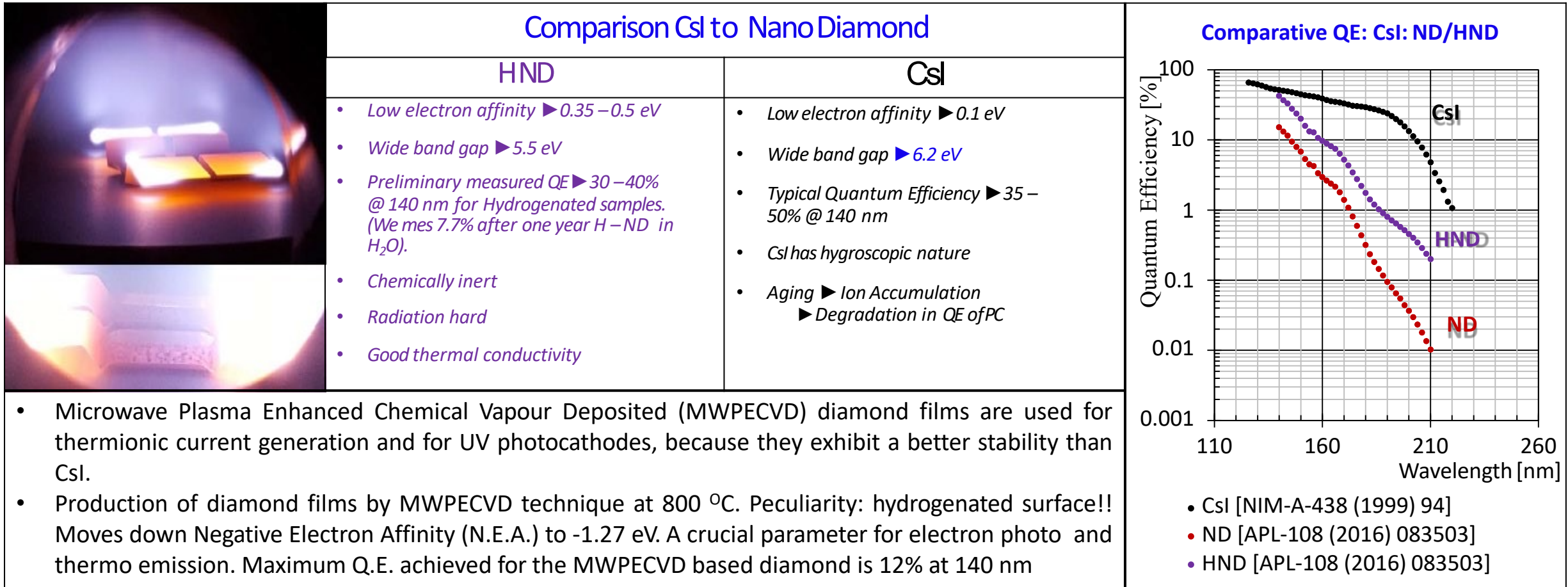
***On Behalf of Trieste,
Bari, & CERN
collaboration***



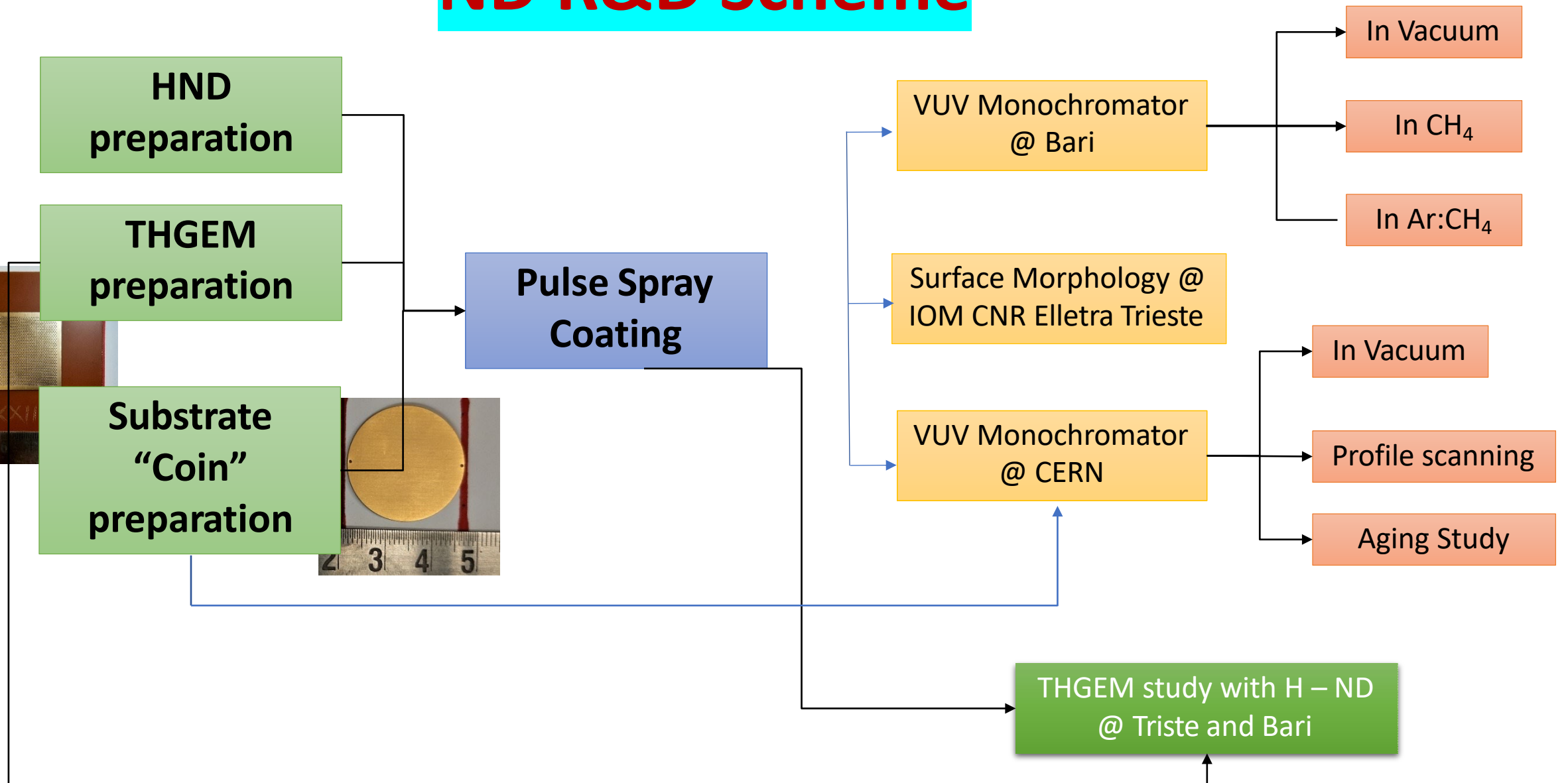
- Introduction
- Hydrogenation and coating
- Pervious studies on HND
- Transmittance of HND
- Photoemission measurement
- Summary

Why and which Nano Diamond

in the framework R&D programme, coupling of H-ND and THGEMs are investigated



ND R&D Scheme



Hydrogenation and Photocathode coating at INFN Bari

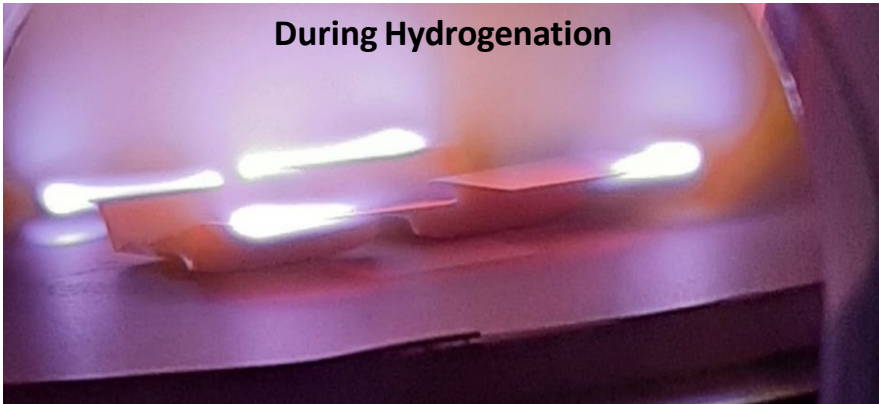
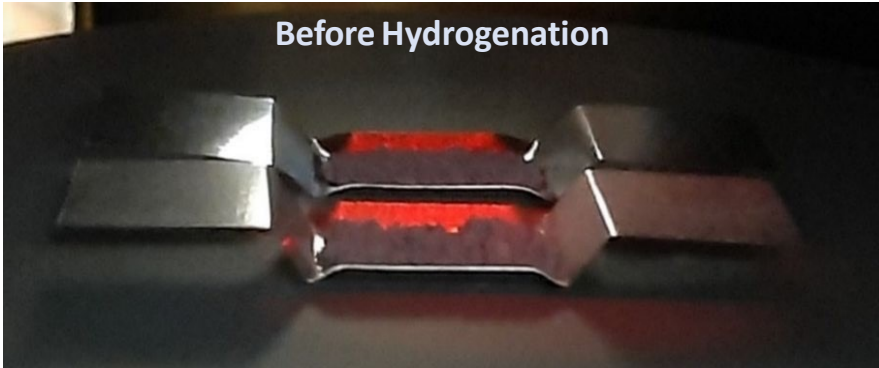
- ND coating by pulsed spray technique

Hydrogenation of ND: MWPECVD setup @ INFN Bari

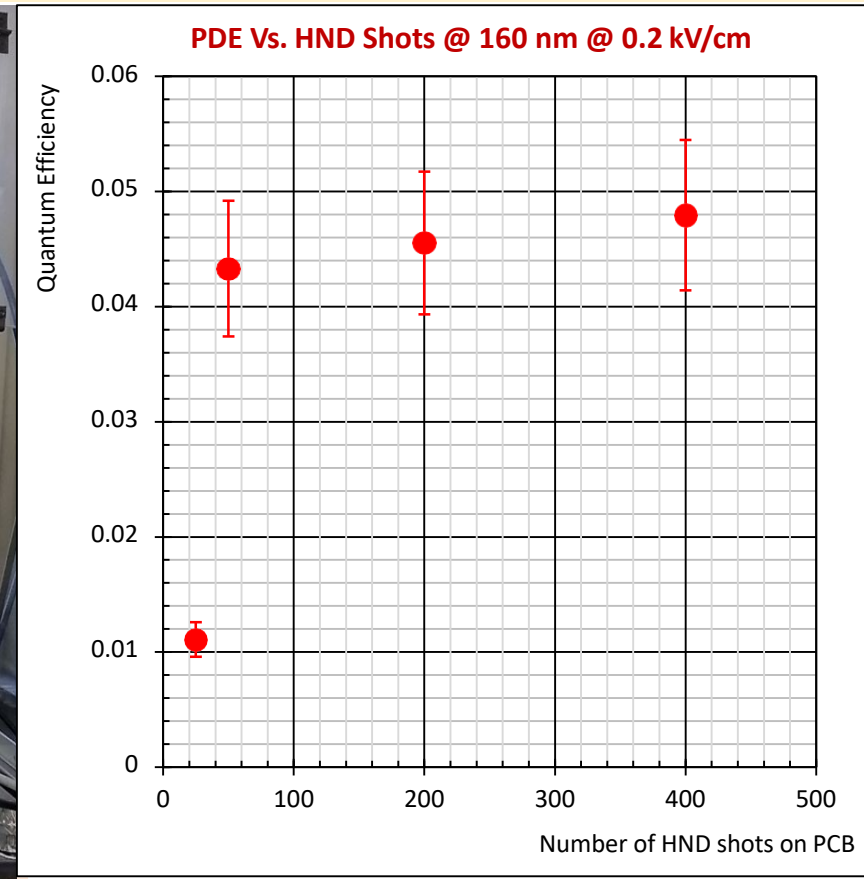
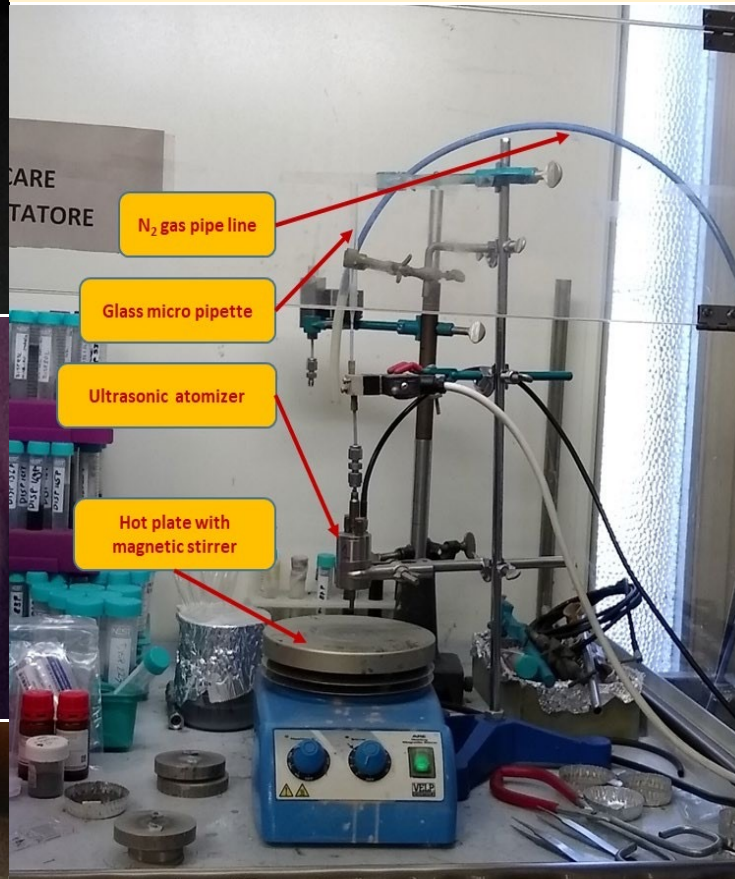
Hydrogenation details:

- Order of vacuum $\sim 6.5 \times 10^{-6}$ mbar.
- 70 mm distance kept between H₂ source and ND powder.
- H₂ gas is generated by electrolysis process using distilled water & H₂ gas flow rate controlled to 200 sccm.
- Hydrogenation of ND powder is performed for 1 hour @ 43 mbar pressure.
- 1380 W microwave power used to reach 1000 °C temperature with 830 °C substrate holder temperature.
- 1250 W microwave power used to reach 810 °C temperature with 650 °C substrate holder temperature.

Hydrogenation & Coating of ND : @ INFN Bari



Pulsed spray thin film coating setup: No of Shots determine the coating thickness



Types of Nano-Diamond Powder

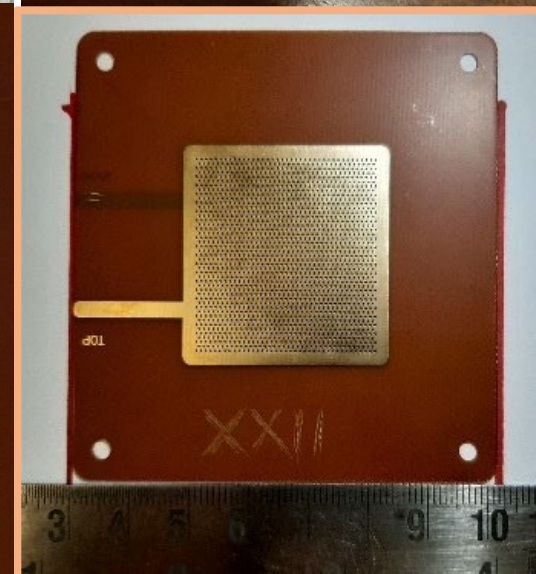
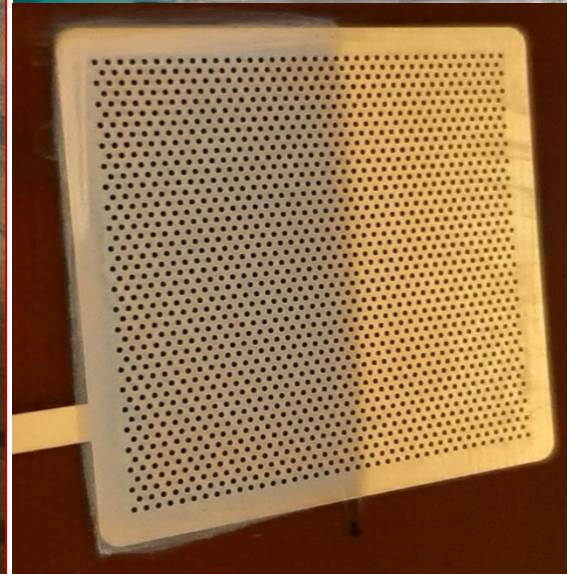
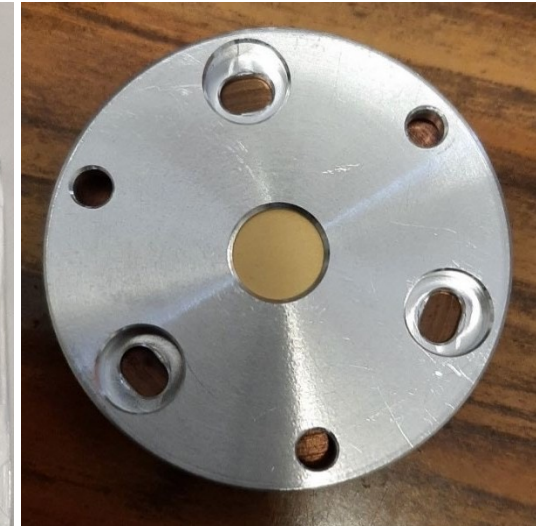
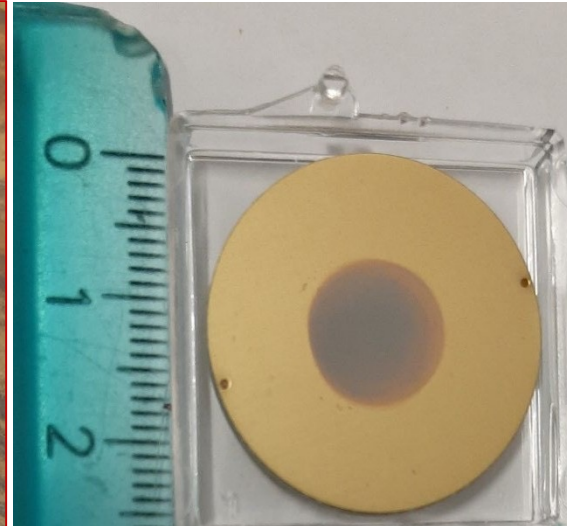
- ND - D&T
- ND - E6
- ND - BDD

[ChangSha 3 Better Ultra-hard materials Co.,LTD]
SONICATED in distilled water with 1:1 ratio

Coating Details:

- For all PCB/Substrate : 1000 shots on 10 mm diameter area
- Each shot duration : 250 mSec
- Pause duration after each shot : 1000 mSec
- Temperature : 150 °C
- Distance between substrate and PSC spray point : 10 mm

NDs solutions & their coating



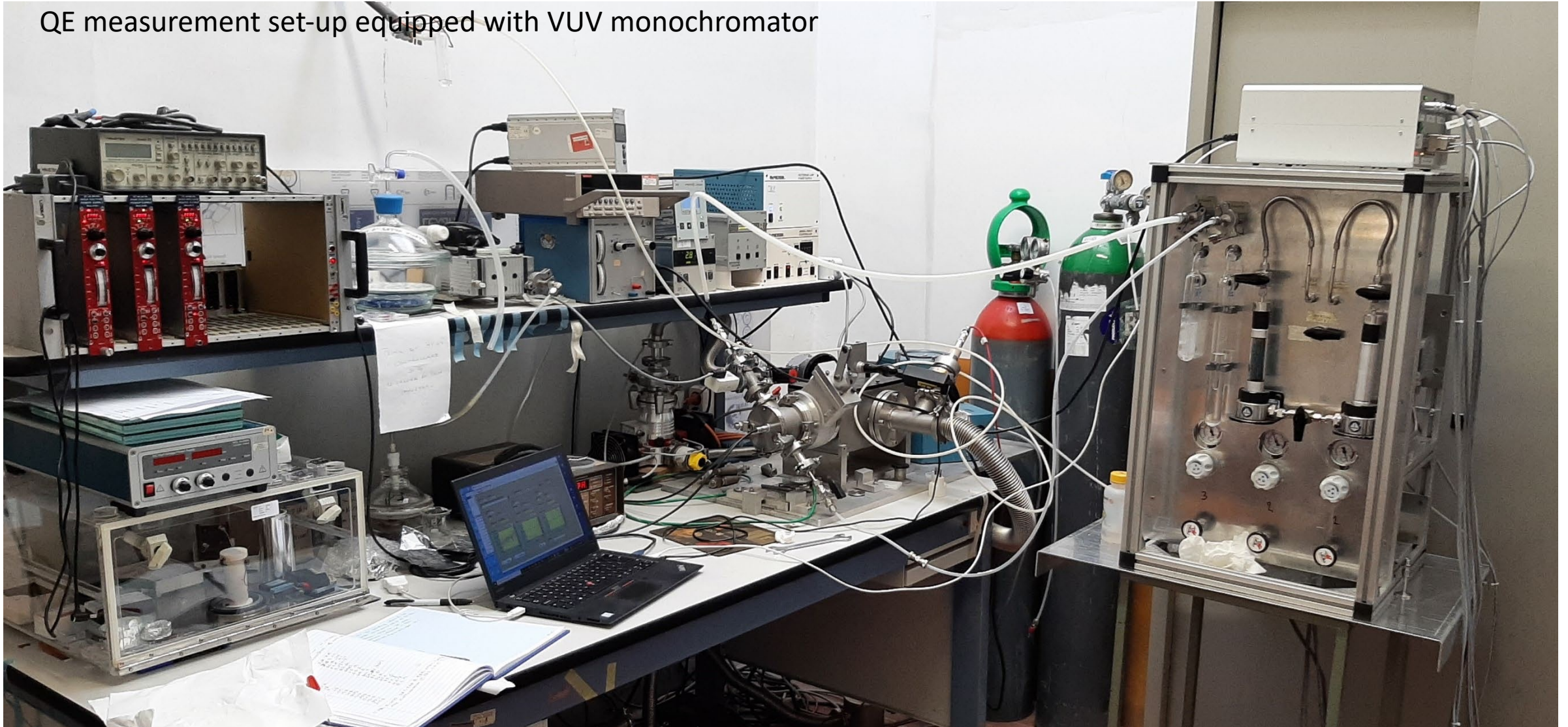
Coated THGEMs and PCB Coins

- ND & HND coted on 14 PCB coins
- ND & HND coted on 06 TEM Grids
- Non-hydrogenated ND full THGEMs (Four)
- Hydrogenated ND full THGEMs (Five)

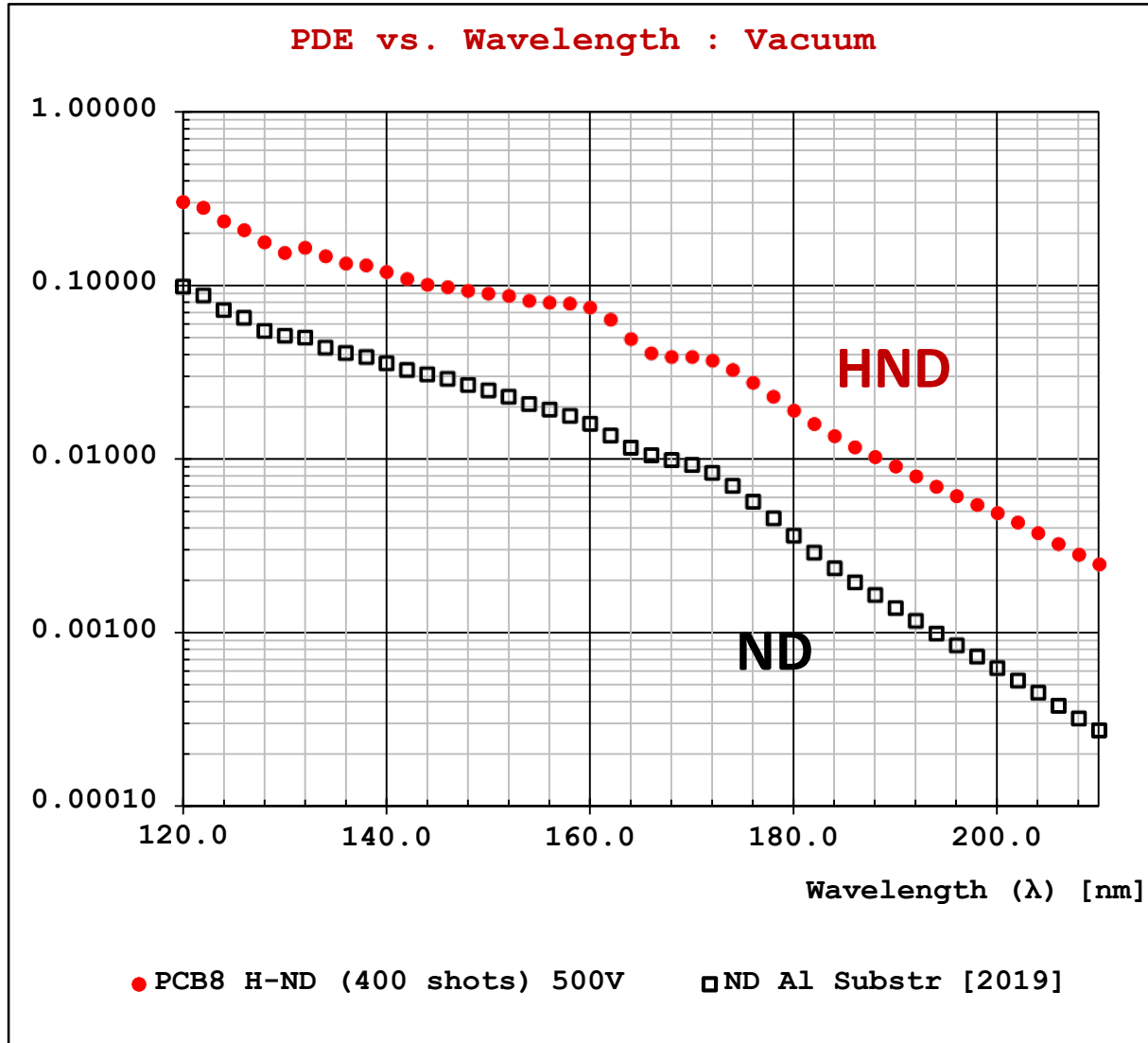
Photoemission measurements

Photoemission setup and gas mixing unit

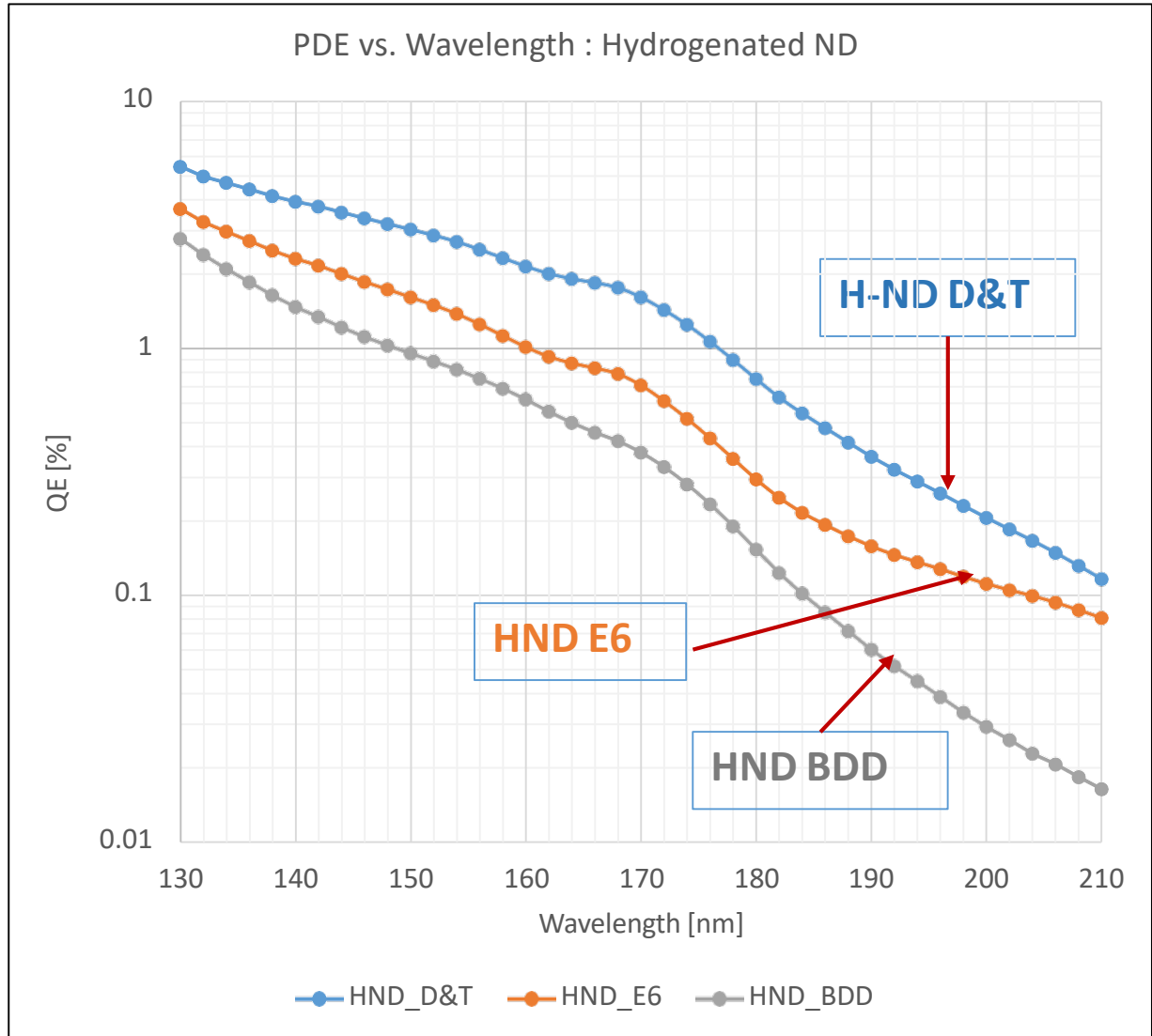
QE measurement set-up equipped with VUV monochromator



OLD ND, HND [D&T]- 2019



New HND [D&T, E6, and BDD]- 2021

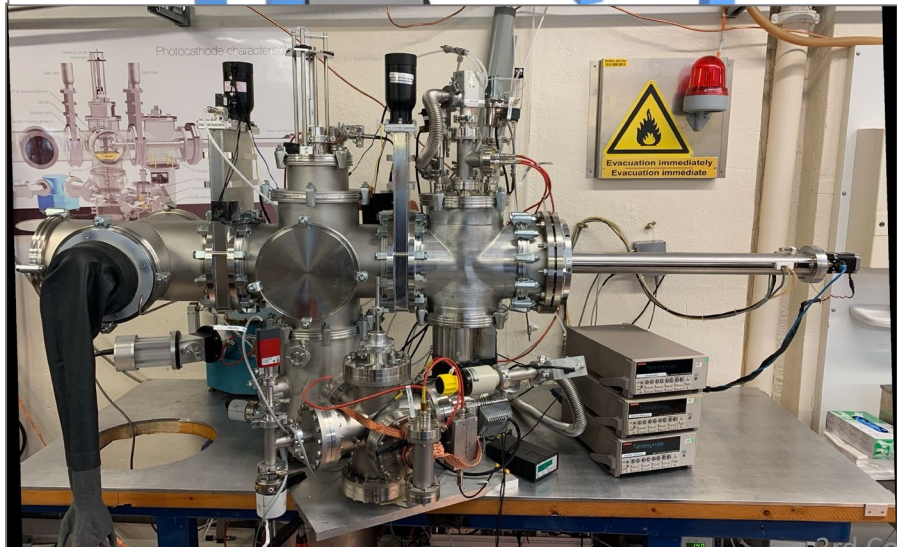
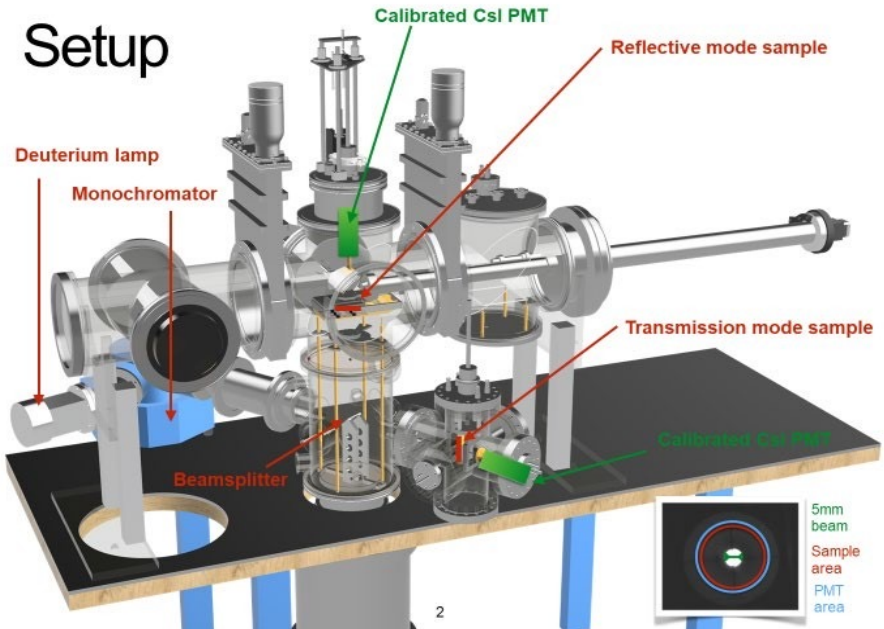


***Photocurrent values : H-ND Old/H-ND new factor ~3 for Vacuum @160 nm**

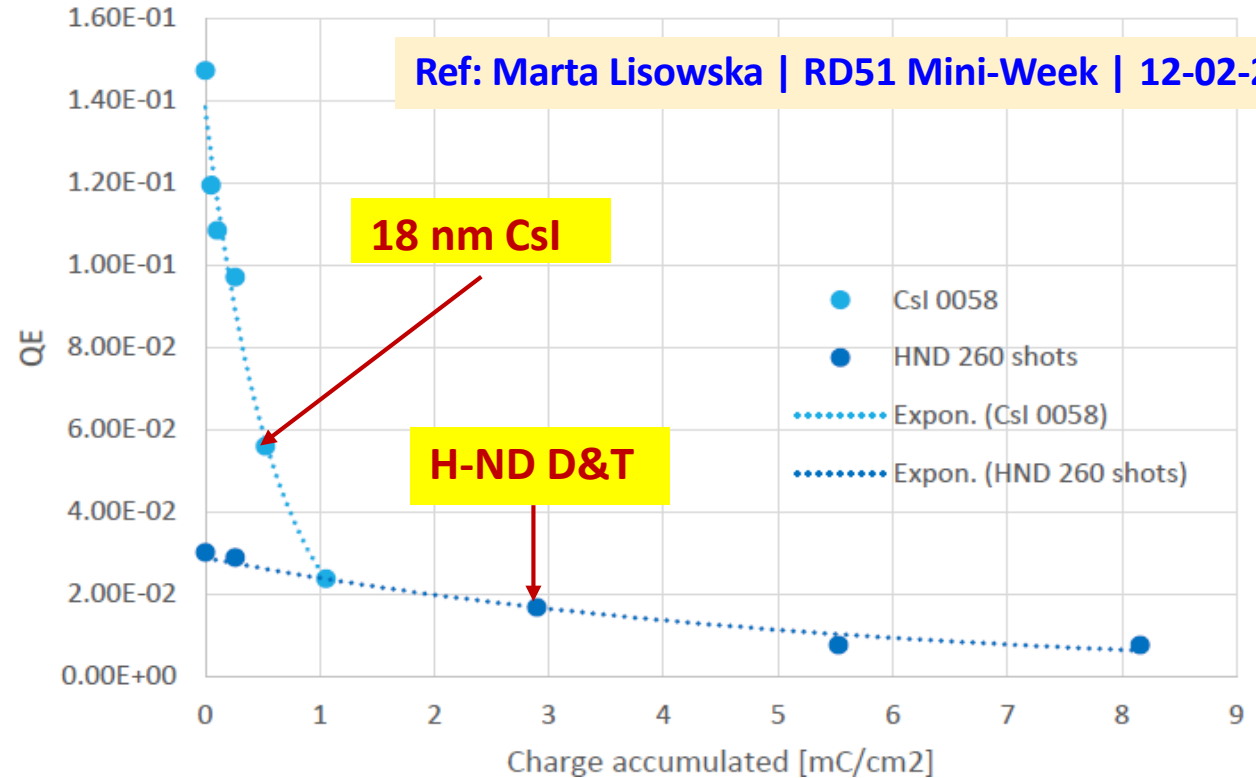
Schematic & Pictorial view of photoemission measurement setup: ASSET @ RD51 CERN

Aging study with X-Ray irradiation of HND PC @ RD51 CERN

Setup



QE vs Charge accumulated @ 160 nm



Ref: Marta Lisowska | RD51 Mini-Week | 12-02-2020

18 nm CsI

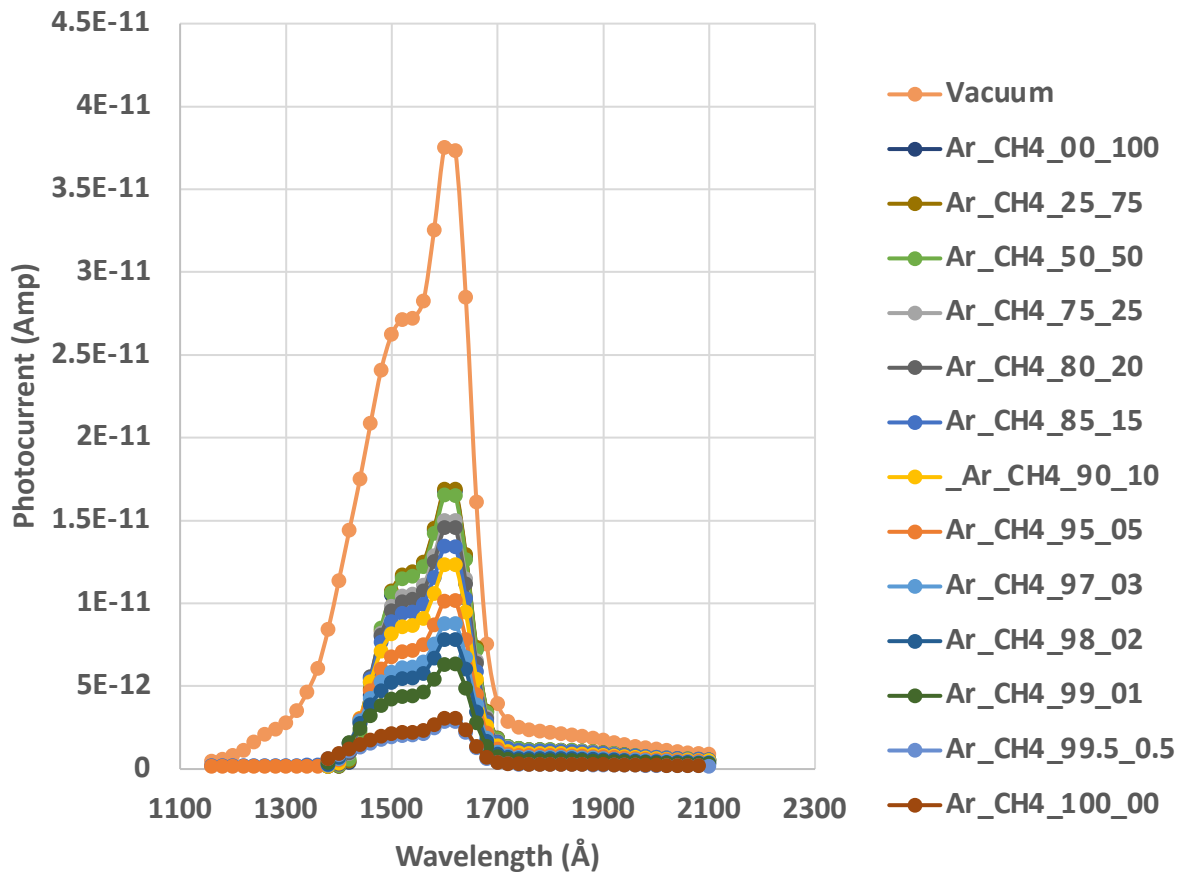
H-ND D&T

- ❑ This is the first preliminary irradiation ageing study of HND photocathodes ever performed.
- ❑ HND photocathodes are quite robust compared to CsI to X-ray Irradiation
- ❑ CsI PDE lowered down by factor ~5 at 1 mC/cm² of charge accumulation

Wavelength Scan: @ 90 V [~0.2 kV/cm]

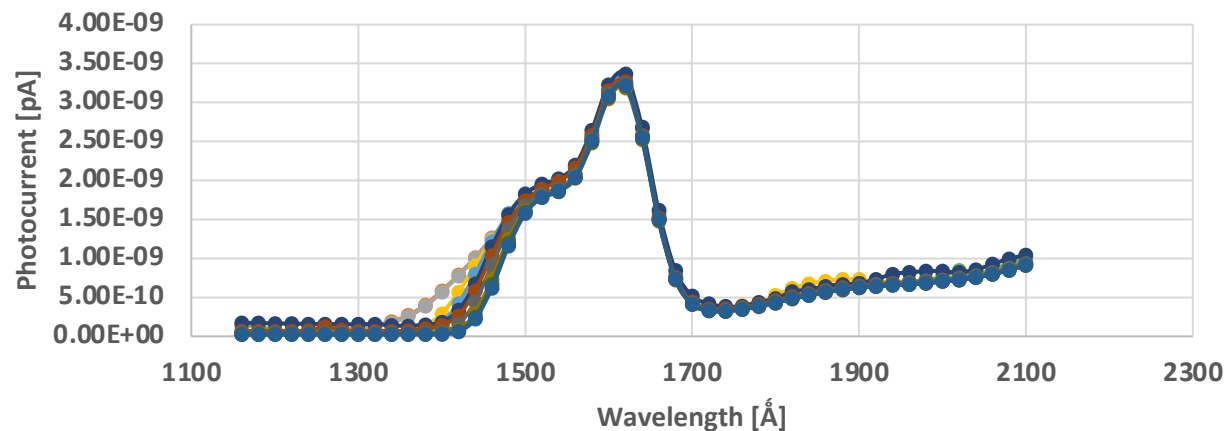
Photocurrent measurement in vacuum and in gas

HND_D&T_1000_0C_PCB4

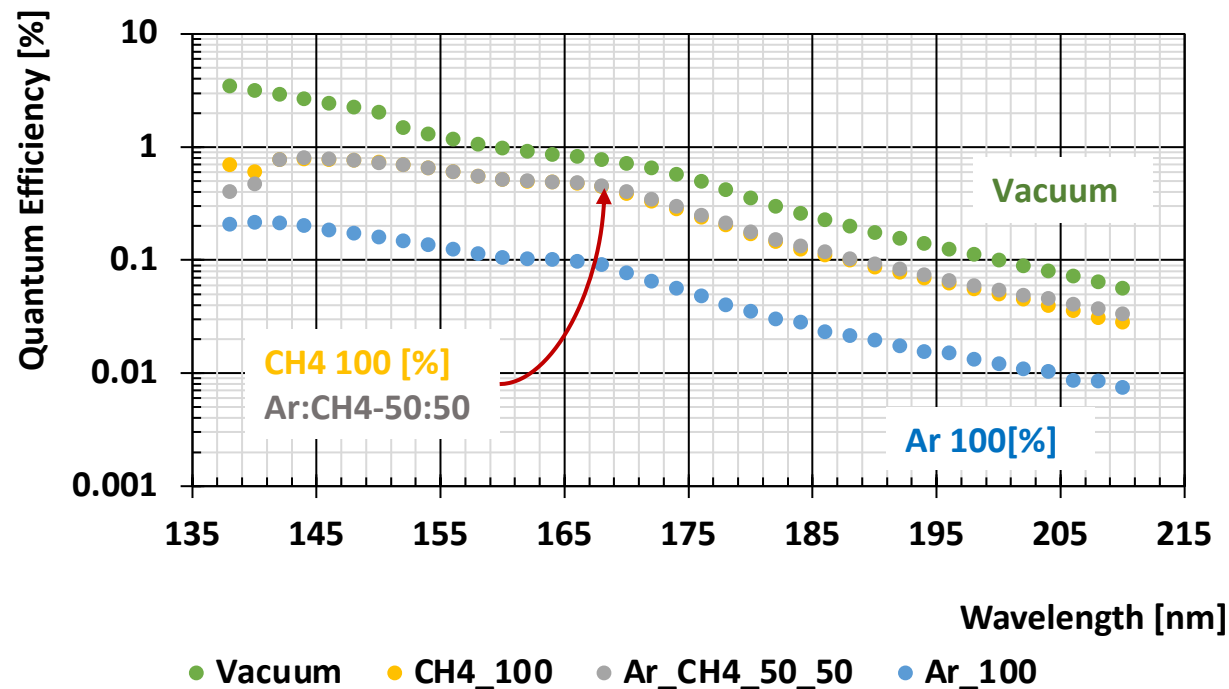


- H-ND from D&T having max QE
- In vacuum QE is max compared to gas mixtures
- QE is min in pure Ar gas & increases with an increase of CH4

Wavelength scan : I_NIST_2017



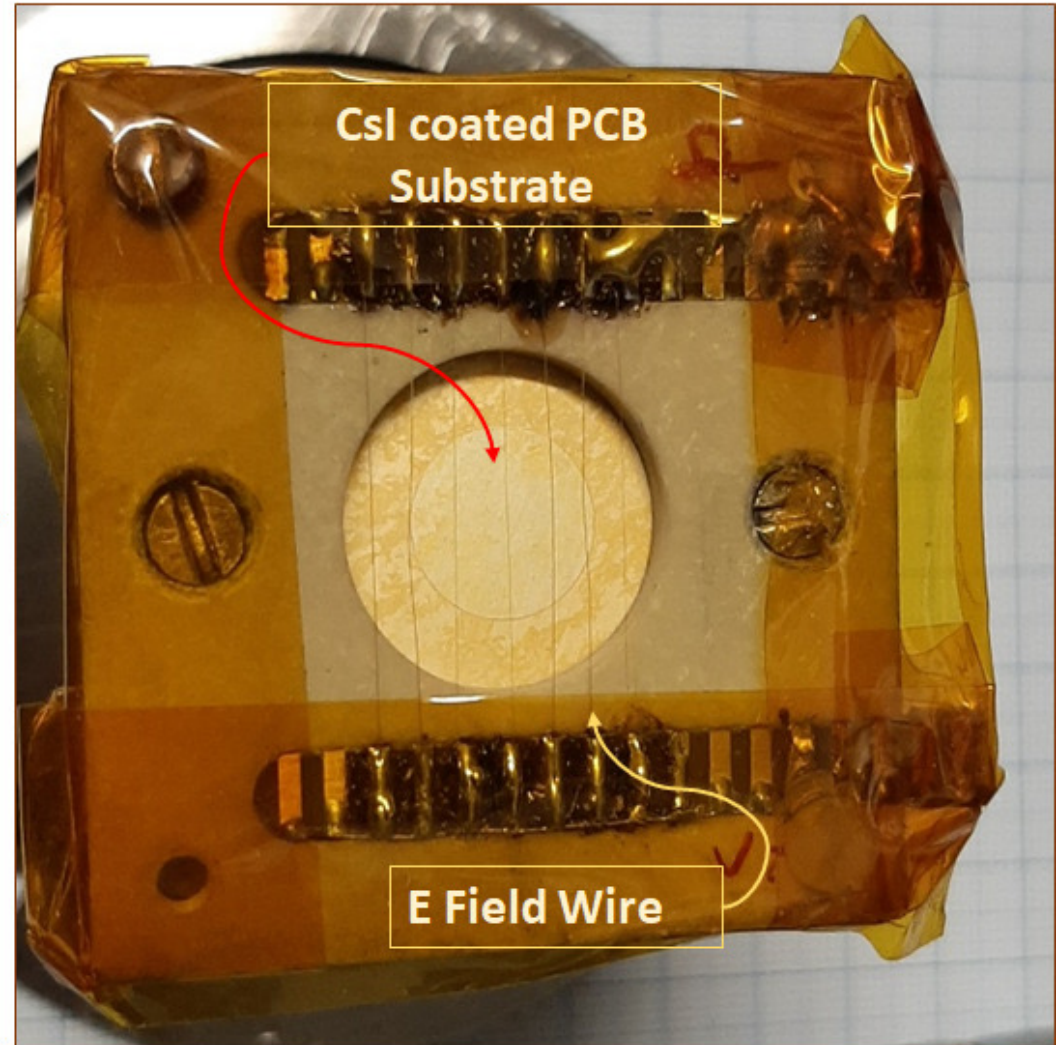
PDE of HND D&T: Vac and gas mixtures



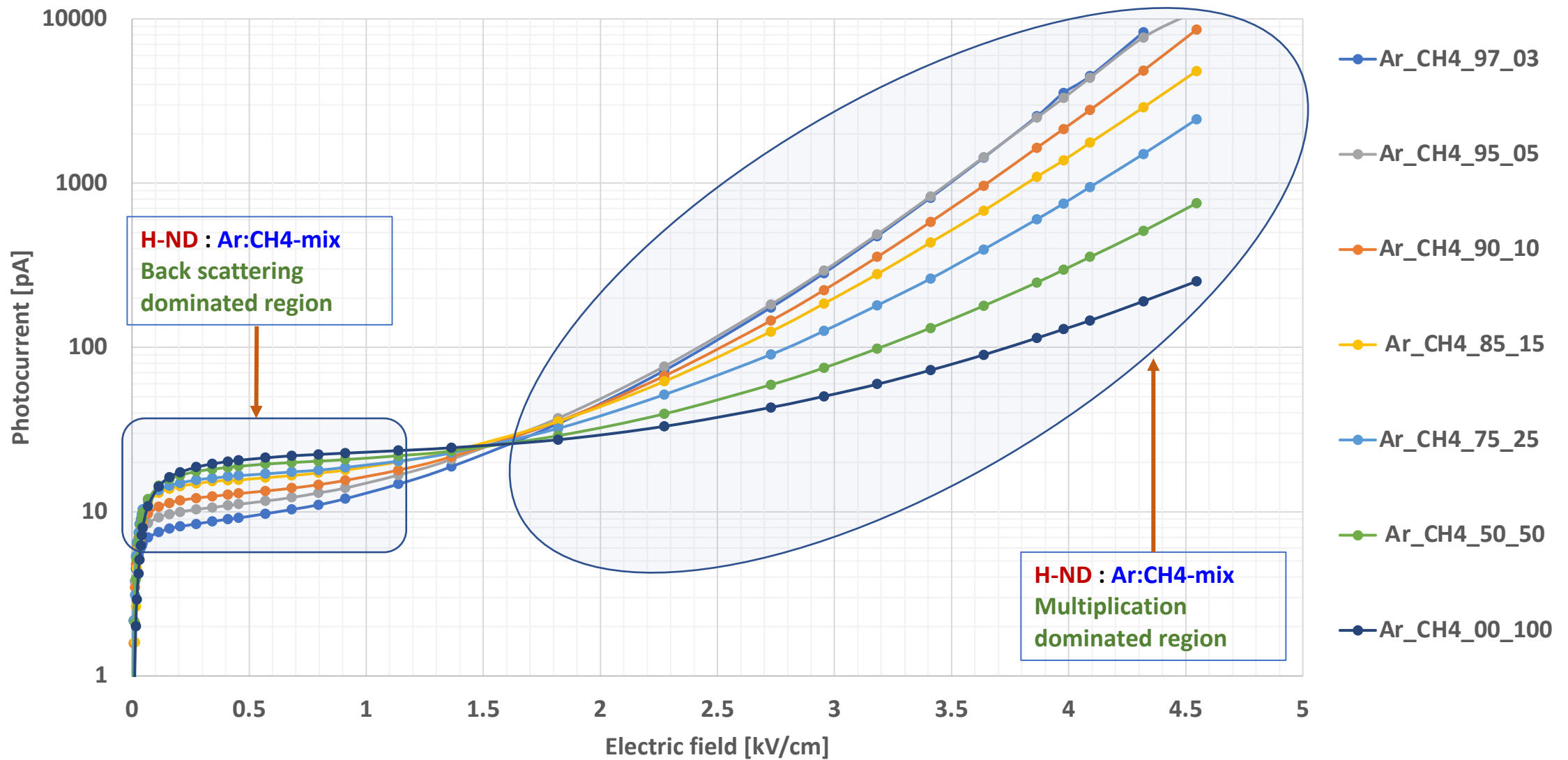
E Field Scan : @ $\lambda = 162$ nm H-ND D&T

- Gap between substrate and electric wire is **4.4 mm**.
- Wavelength is fixed at 162 nm for E filed scan
- Wavelength scan and E Field scan performed with **MgF2 window** in vacuum as well as in Ar:CH4 gas mixtures

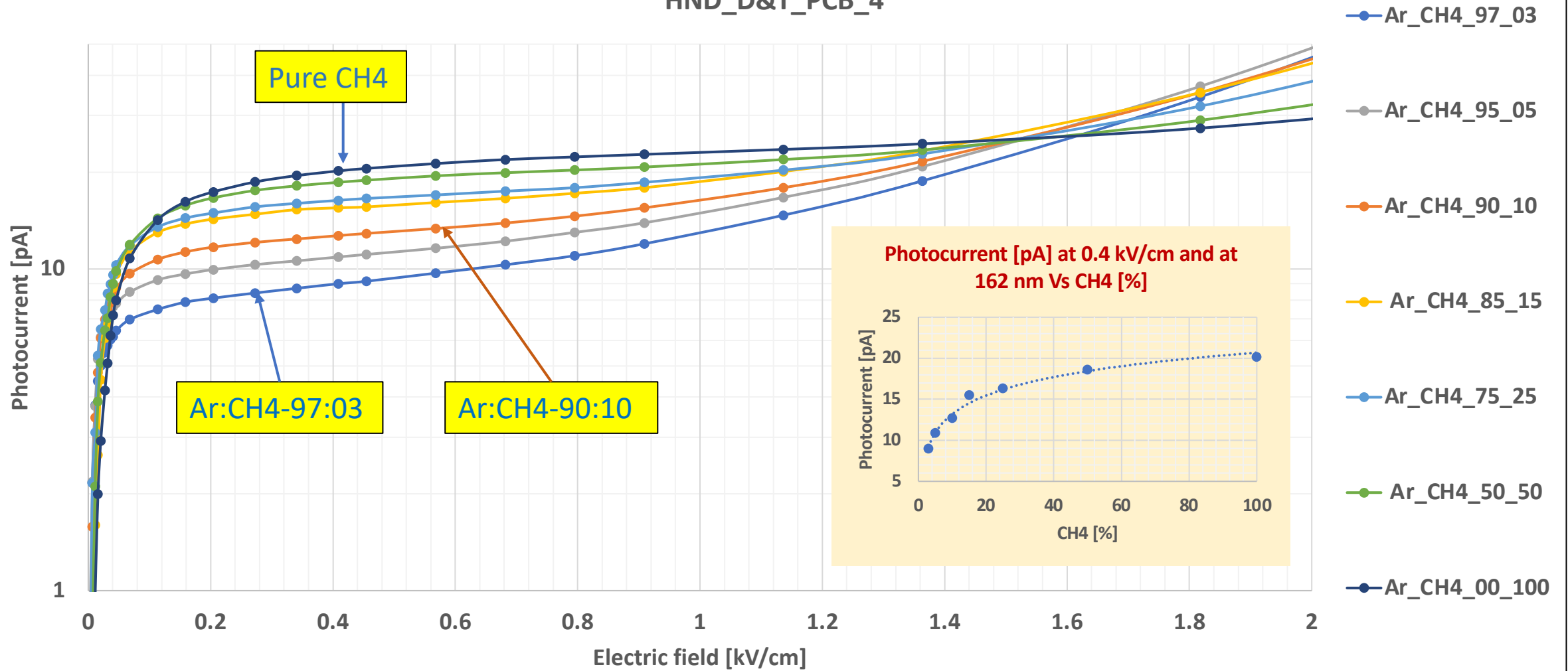
Substrate holder for photo current measurement



HND_D&T @ 162 nm: Photocurrent vs E field for different Ar:CH₄ gas mixtures



HND_D&T_PCB_4

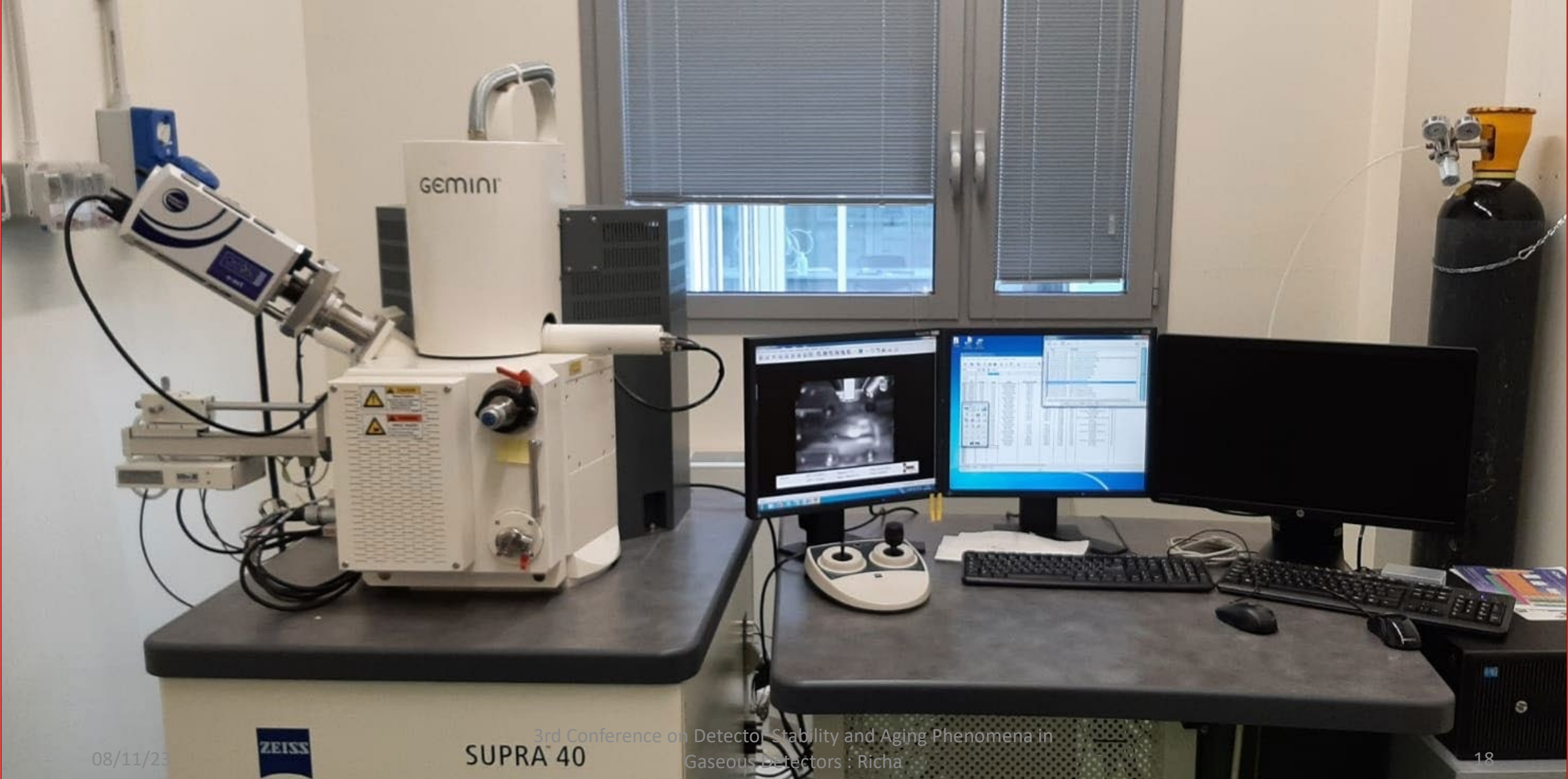


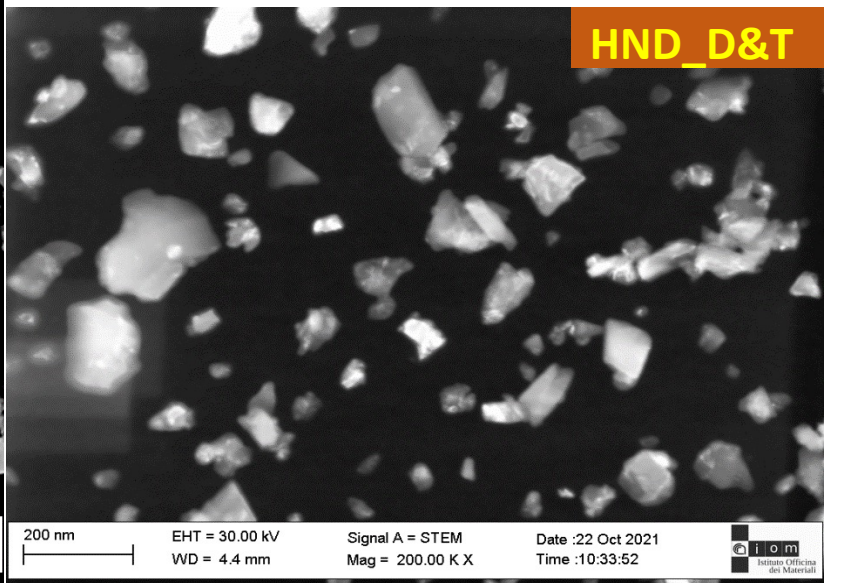
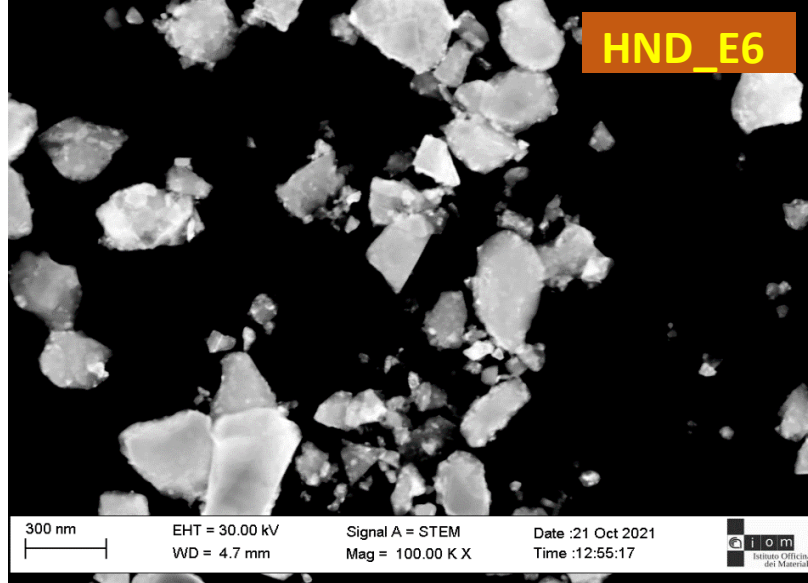
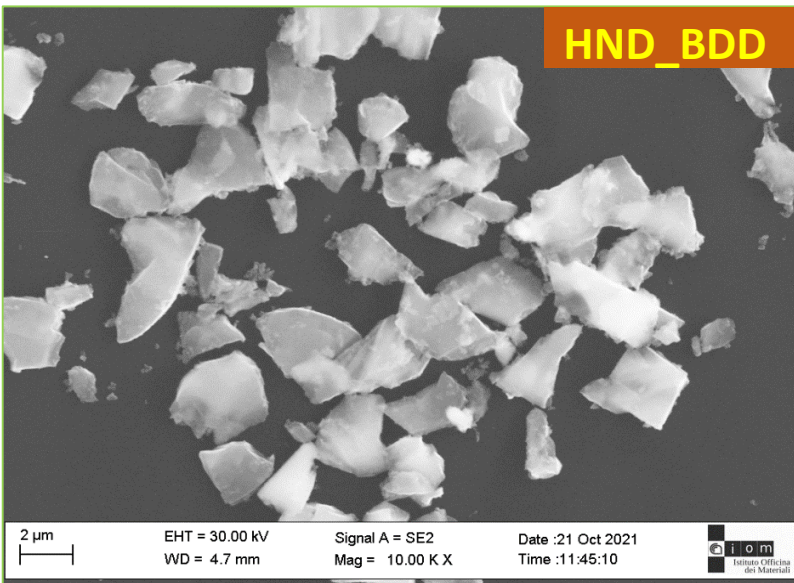
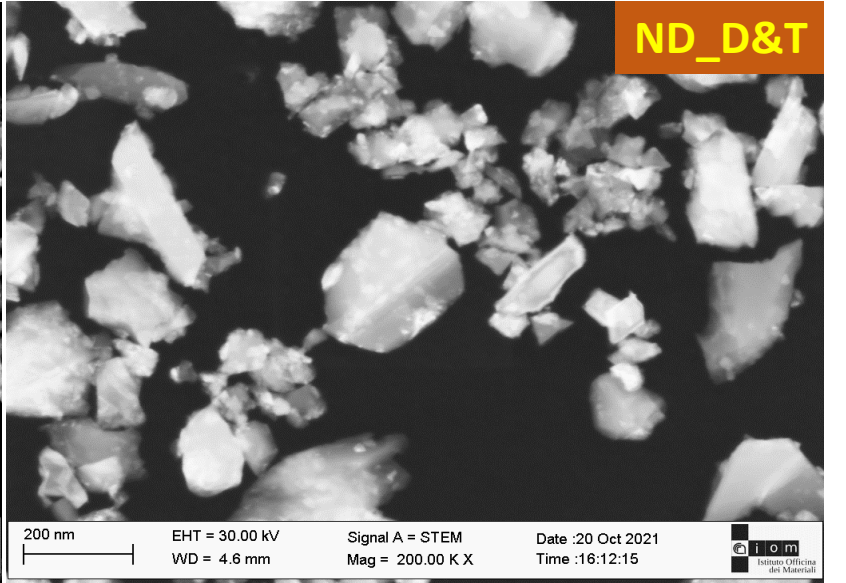
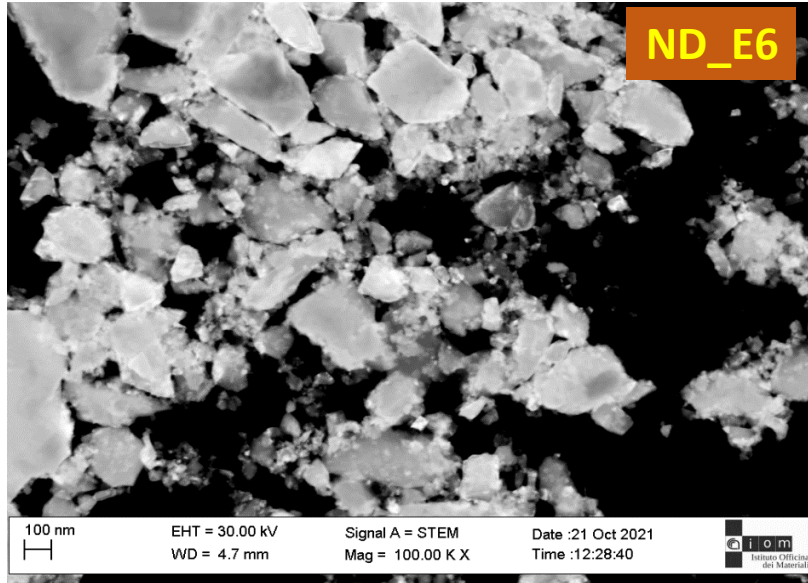
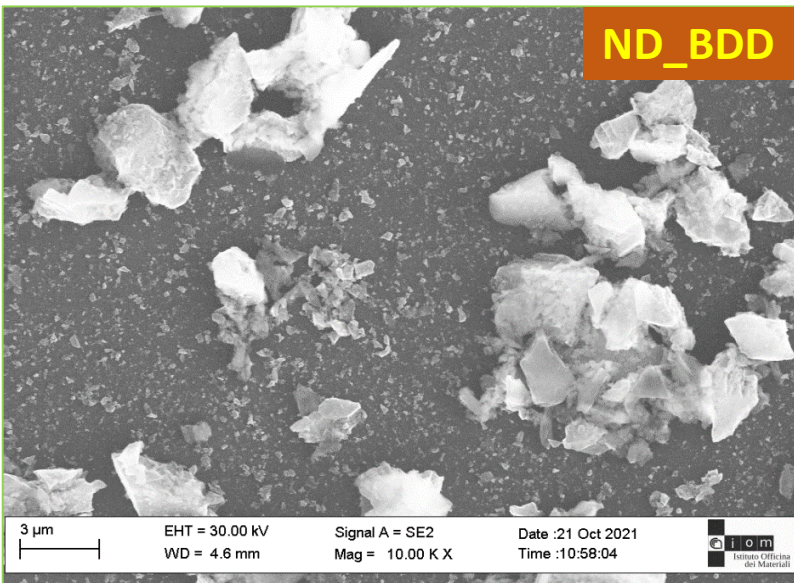
- ❑ Ar:CH4_50:50 ~9% lower PDE compared to Pure CH4
- ❑ Ar:CH4_75:25 ~24% lower PDE compared to Pure CH4
- ❑ Ar:CH4_97:03 ~55% lower PDE compared to Pure CH4

Surface morphology analysis of NDs by Scanning /Transmission electron microscopy

@ IOM CNR Elletra – Trieste Italy

SEM/STEM setup @ IOM-CNR, Elletra





STEM images of 10 shots of ND and HND powders coated on TEM grid.

THGEM with Nanodiamond Photocathode

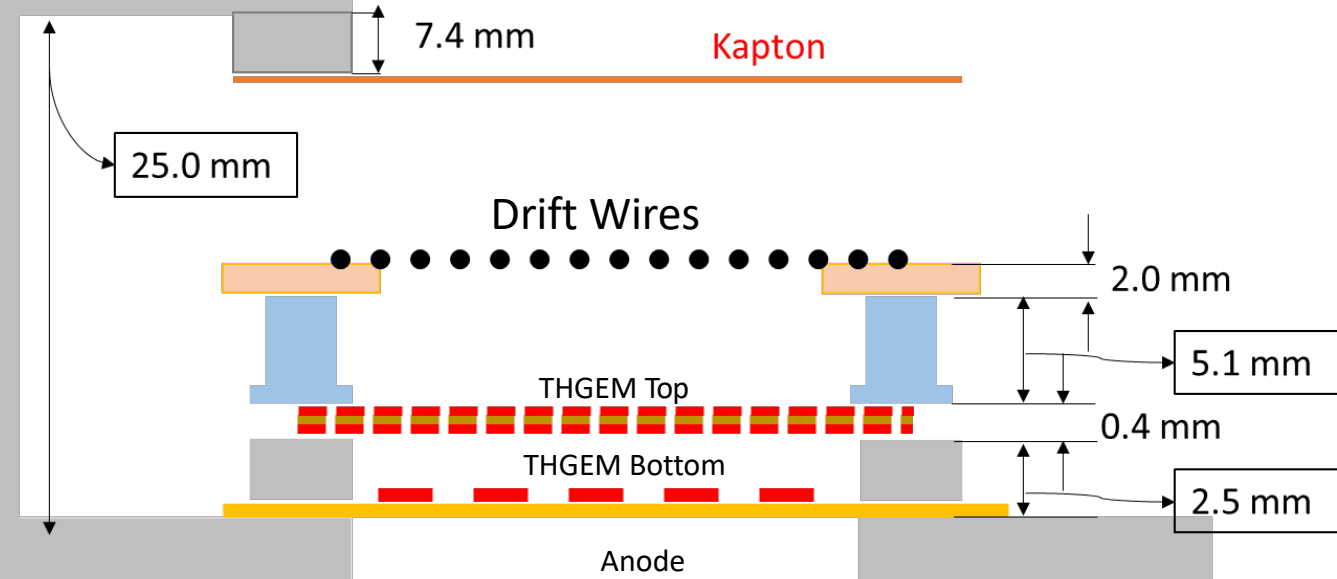
Thickness (t) = 0.4 mm

Diameter (d) = 0.4 mm

Pitch (p) = 0.8 mm

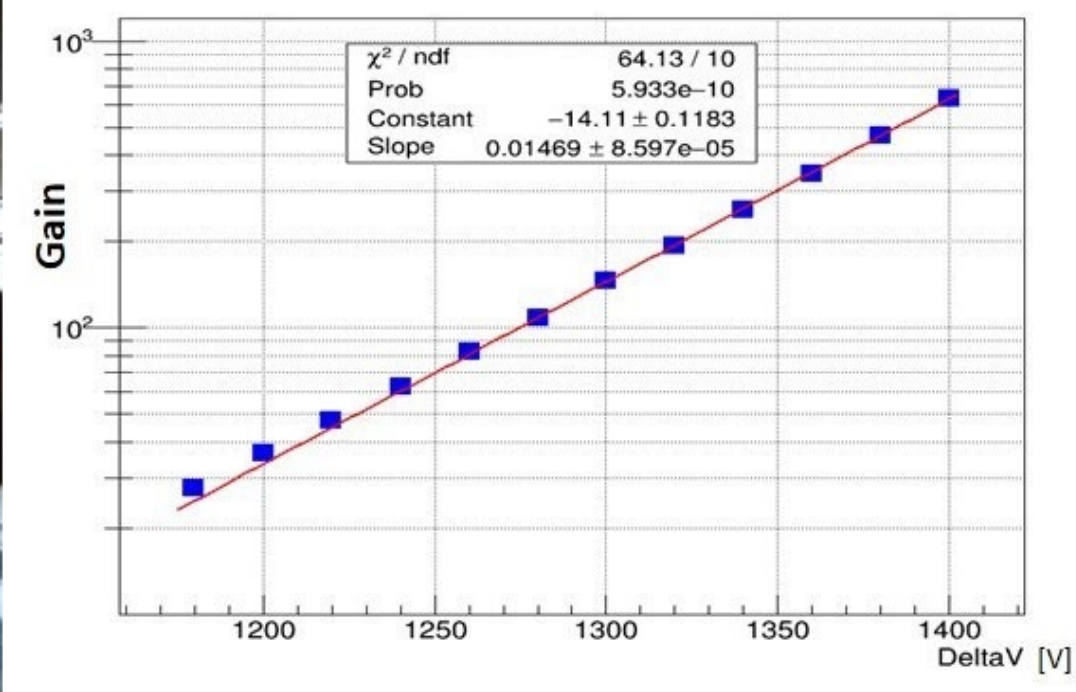
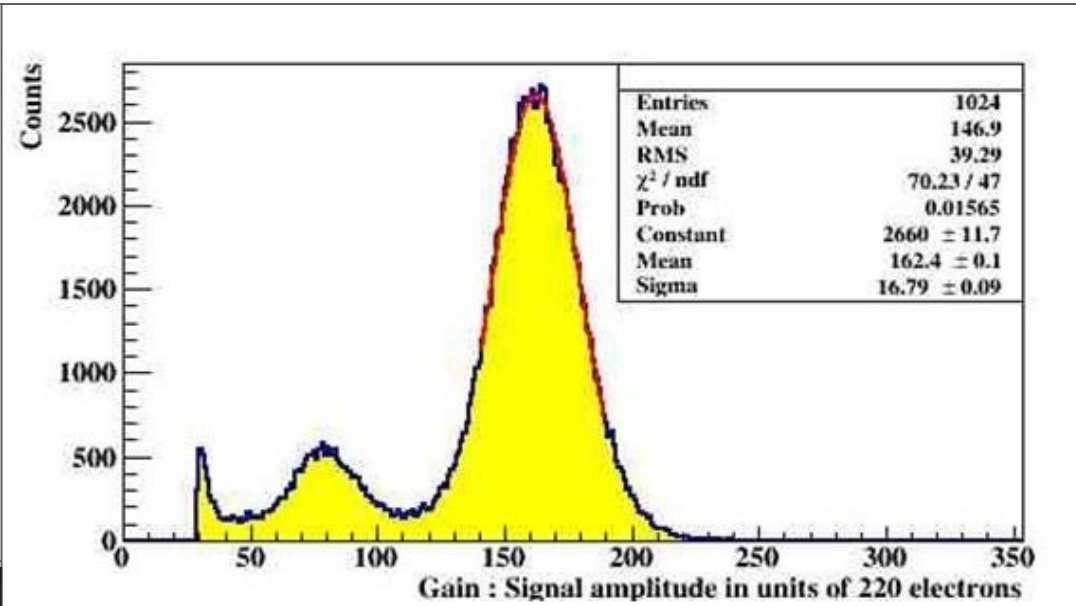
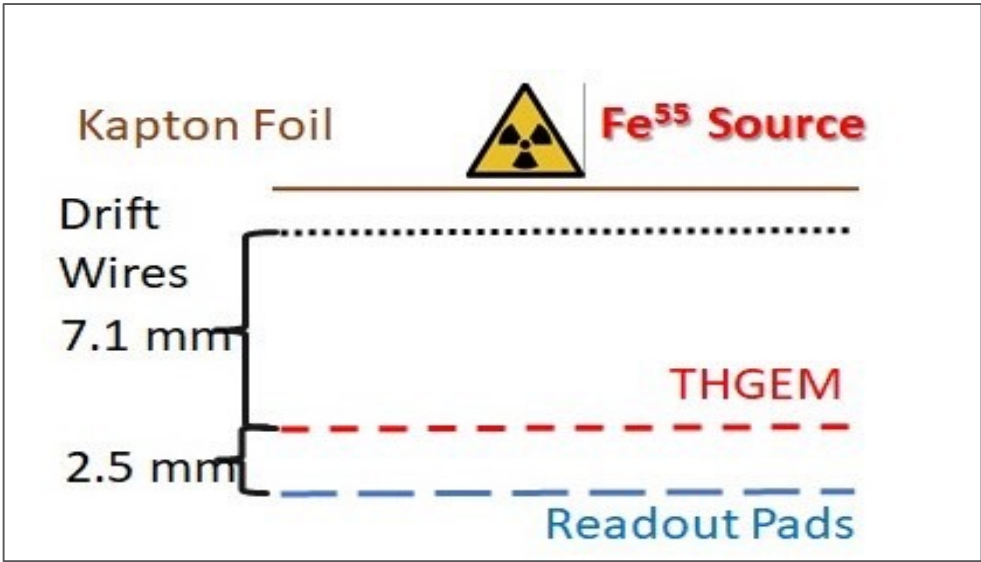
THGEM parameters

Prototype used for measurements (Schematic)



- THGEMs are standard Printed Circuit Boards (PCBs) with holes produced by mechanical drilling.
- Like in GEMs, in the presence of a correct electrical bias and in a proper gas mixture, each hole acts as an electron multiplier.
- The signal generated by the gas multiplication is collected at the anode.
- The geometrical parameters of our THGEMs are: hole diameter (d) = 0.4 mm; hole pitch (p) = 0.8 mm; thickness of the fiberglass (t) = 0.4 mm; and rim around holes < 5 μ m.

- For measurements the gas mixture used is: Ar:CO₂ 70:30
- CAEN N1471H HV PS has been used.
- CREMAT CR-110 Preamplifier with CREMAT CR-150 r5 evaluation board has been used to read the signal from the detector.
- Ortec 672 Spectroscopy amplifier with AMPTEK MCA 8000A has been used for processing the signal and for saving the data.



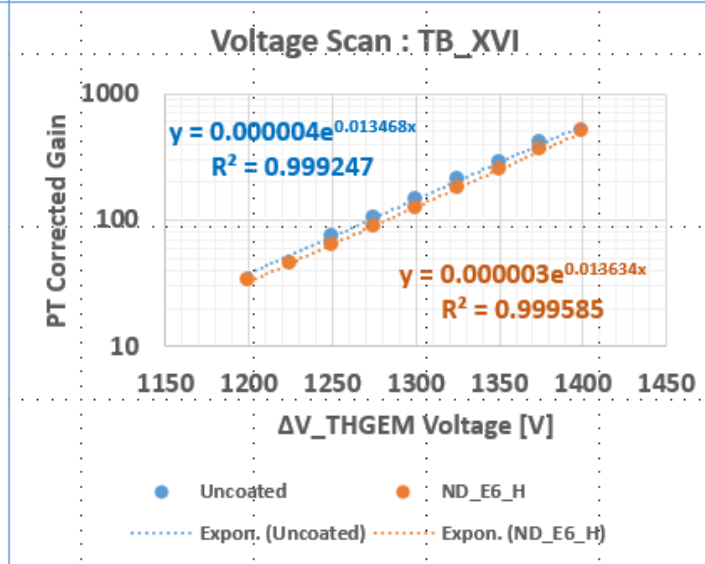
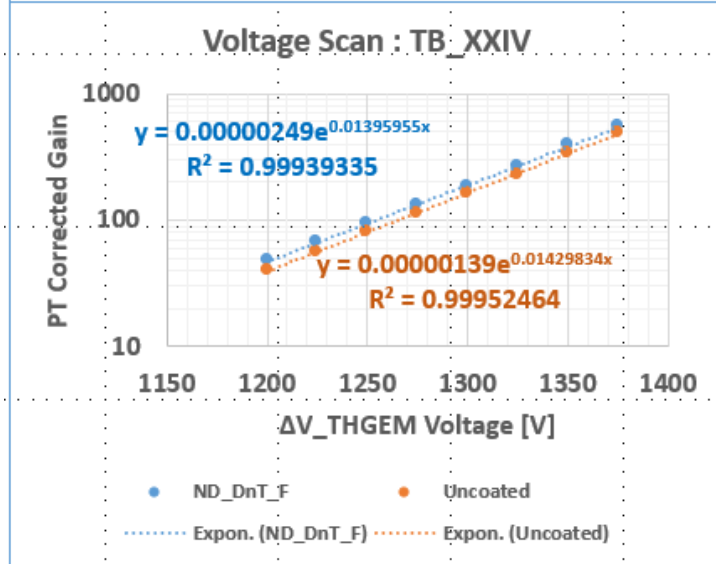
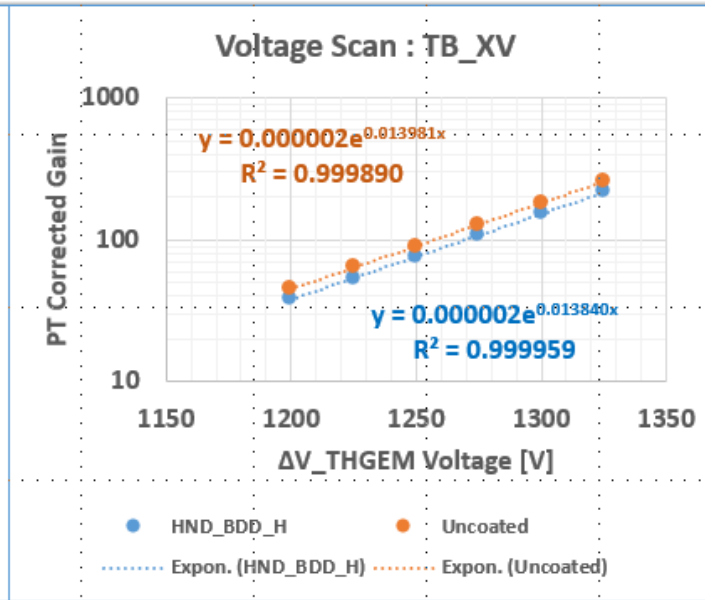
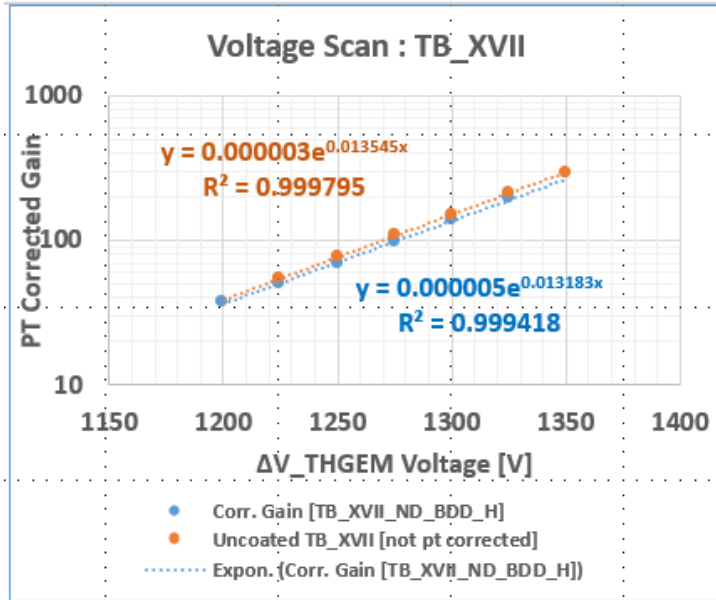
Voltage Applied:
 Drift = 2250 V
 T_{top} = 1750 V
 T_{bot} = 500 V
 Anode = 0 V

Gas Mixture:
 Ar = 70 %
 CO₂ = 30 %
 @ 10 l/h flow rate

X-ray Source:
 Fe-55

THGEM active area:
 30 mm x 30 mm

Electronics used:
 CAEN N1471H HV PS
 CREMAT CR-110 Pre Amp
 ORTEC 672 Amp
 CREMAT CR-150 Eva Board
 AMPTEK MCA 8000A



heat treatment after coating and p/T corrections + charging-up are essential

PT corrected Effective Gain in saturation part

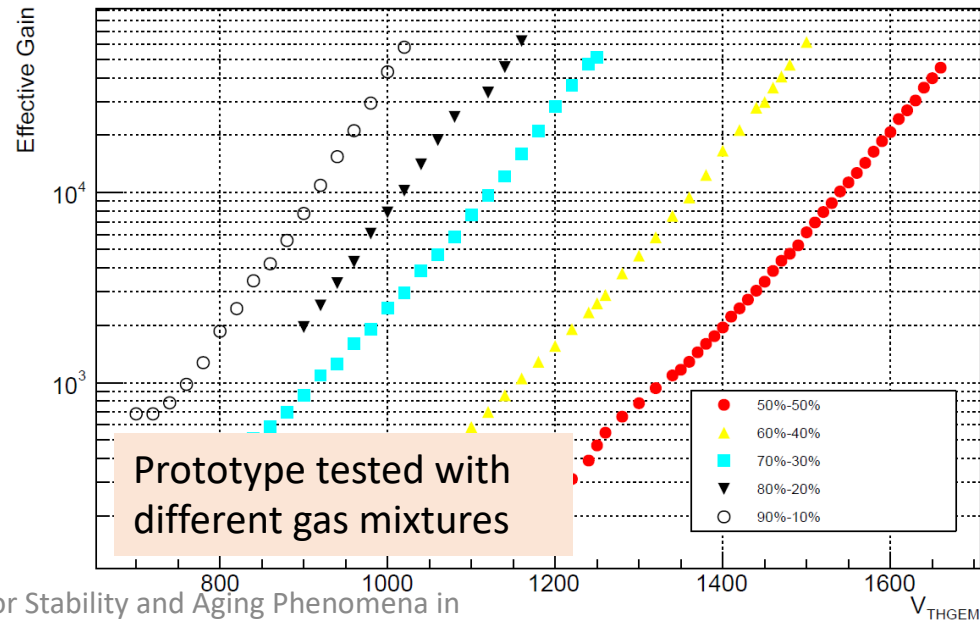
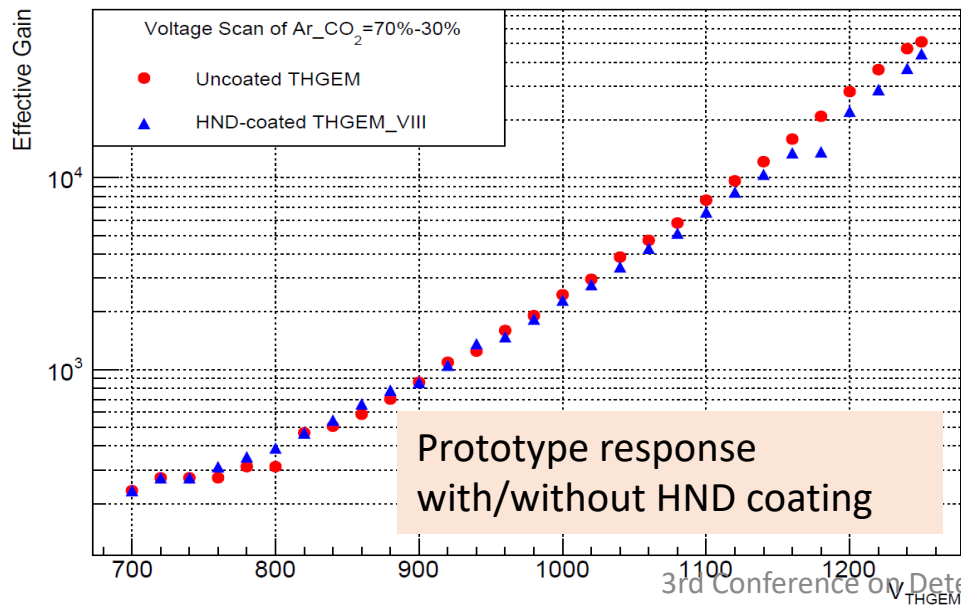
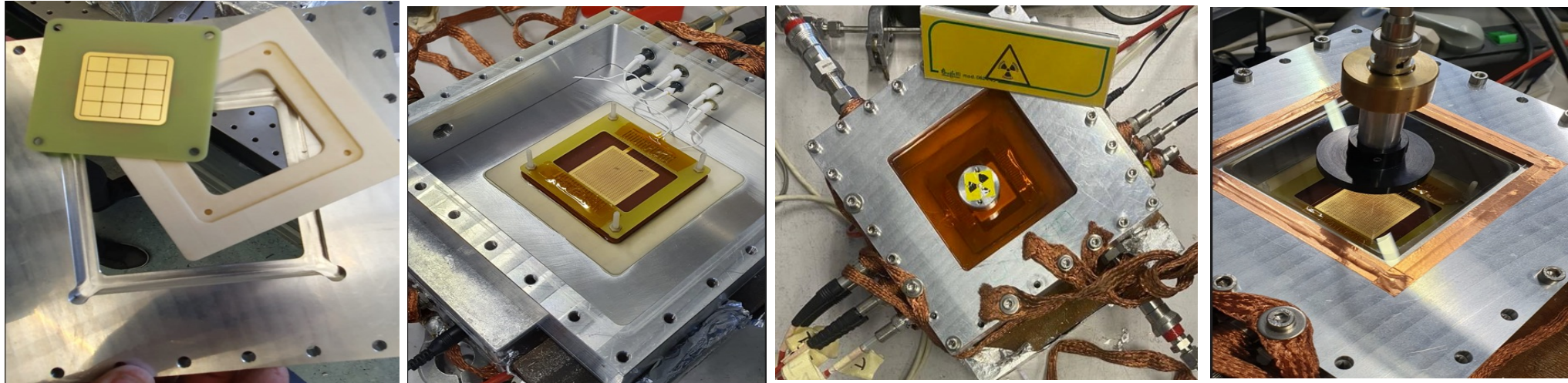
Uncoated THGEMs	Eff. Gain	Coated THGEMs	Eff. Gain	Eff. Gain
TB_XV	82	H-ND_BDD_H	87	+ 6
TB_XVI	75	ND_E6_H	63	- 16
TB_XVII	84	ND_BDD_H	69	- 18
TB_XXIV	82	ND_D&T_F	91	+ 10

Max ΔV_THGEM voltage sustainability

Uncoated THGEMs	Max ΔV THGEM	Coated THGEMs	Max ΔV THGEM
TB_XV	1325	H-ND_BDD_H	1325
TB_XVI	1375	ND_E6_H	1400
TB_XVII	1350	ND_BDD_H	1325
TB_XXIV	1375	ND_D&T_F	1325

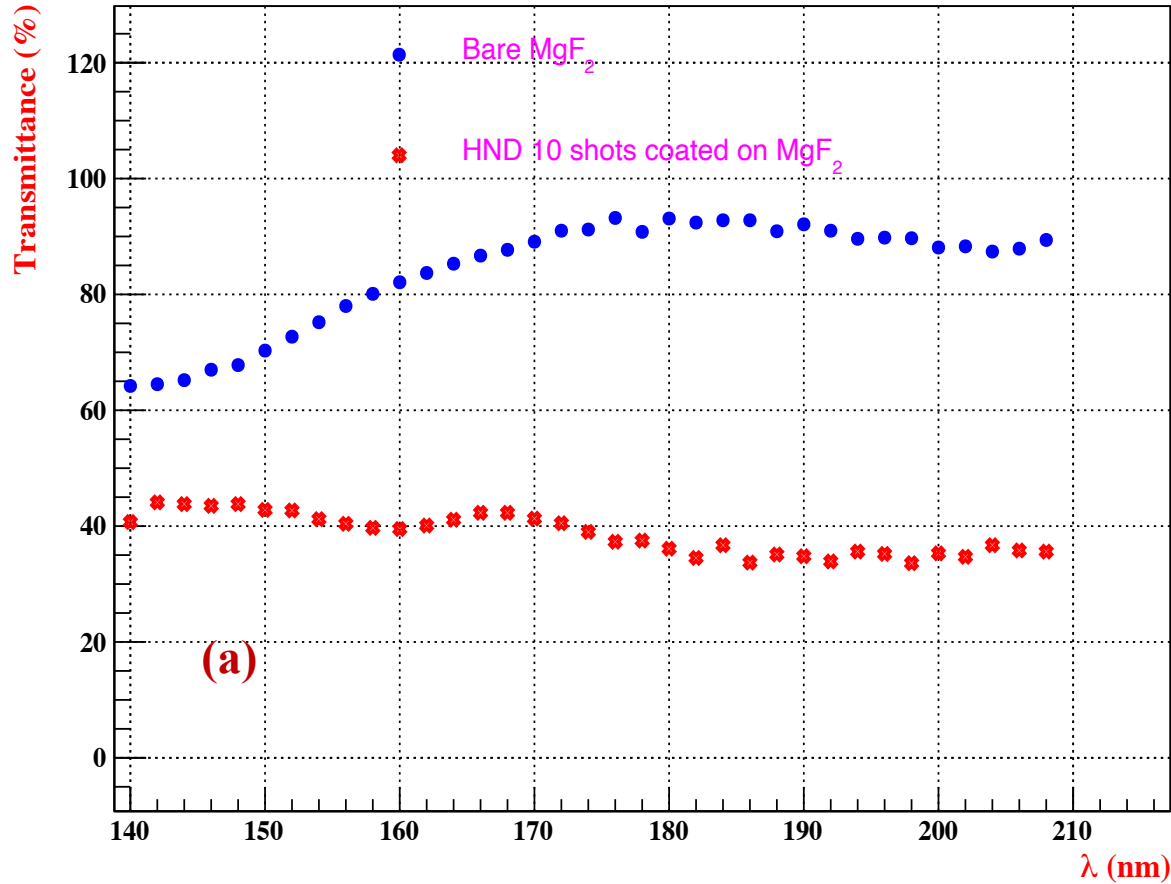
The response of THGEMs as electron multipliers is unaffected by HND coating

HND based prototype of photon detector

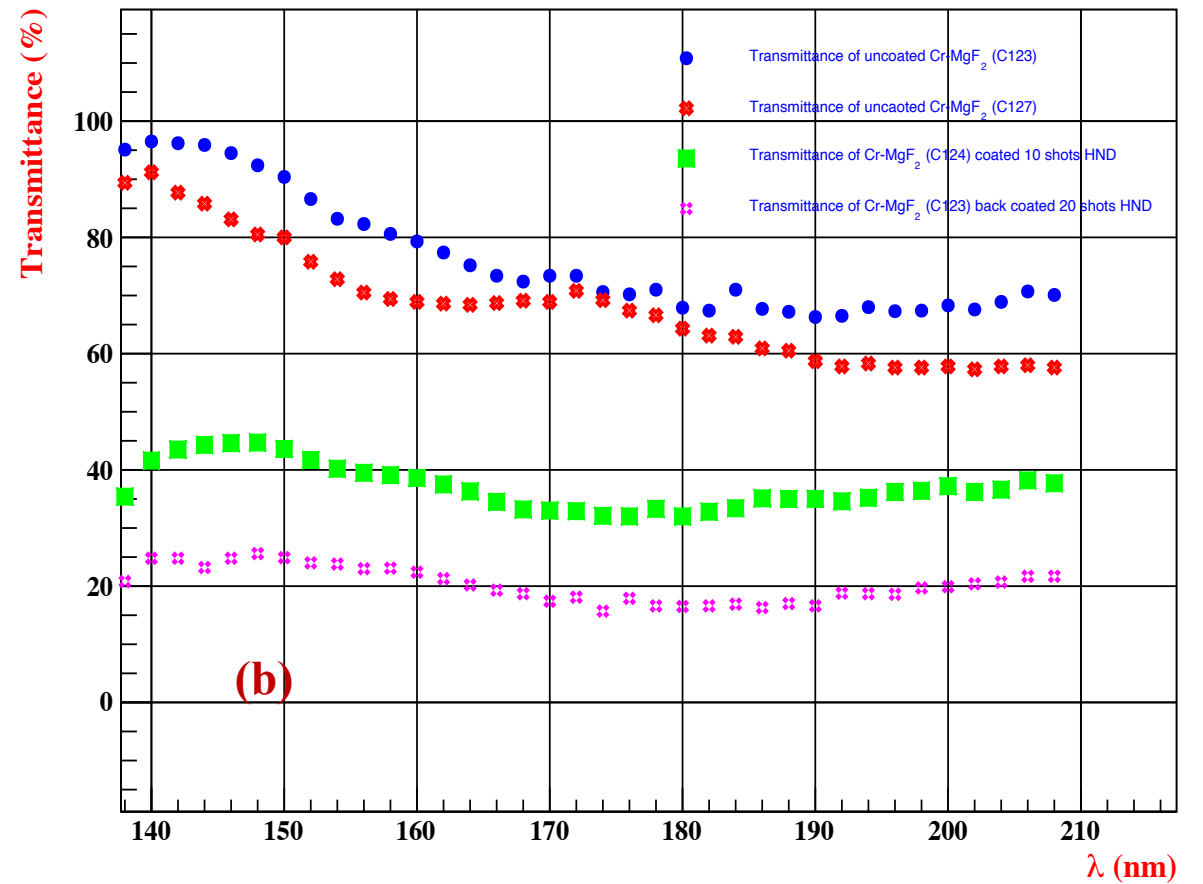


Transmittance of HND coated on MgF_2 and $\text{MgF}_2\text{-Cr}$

Transmittance of HND

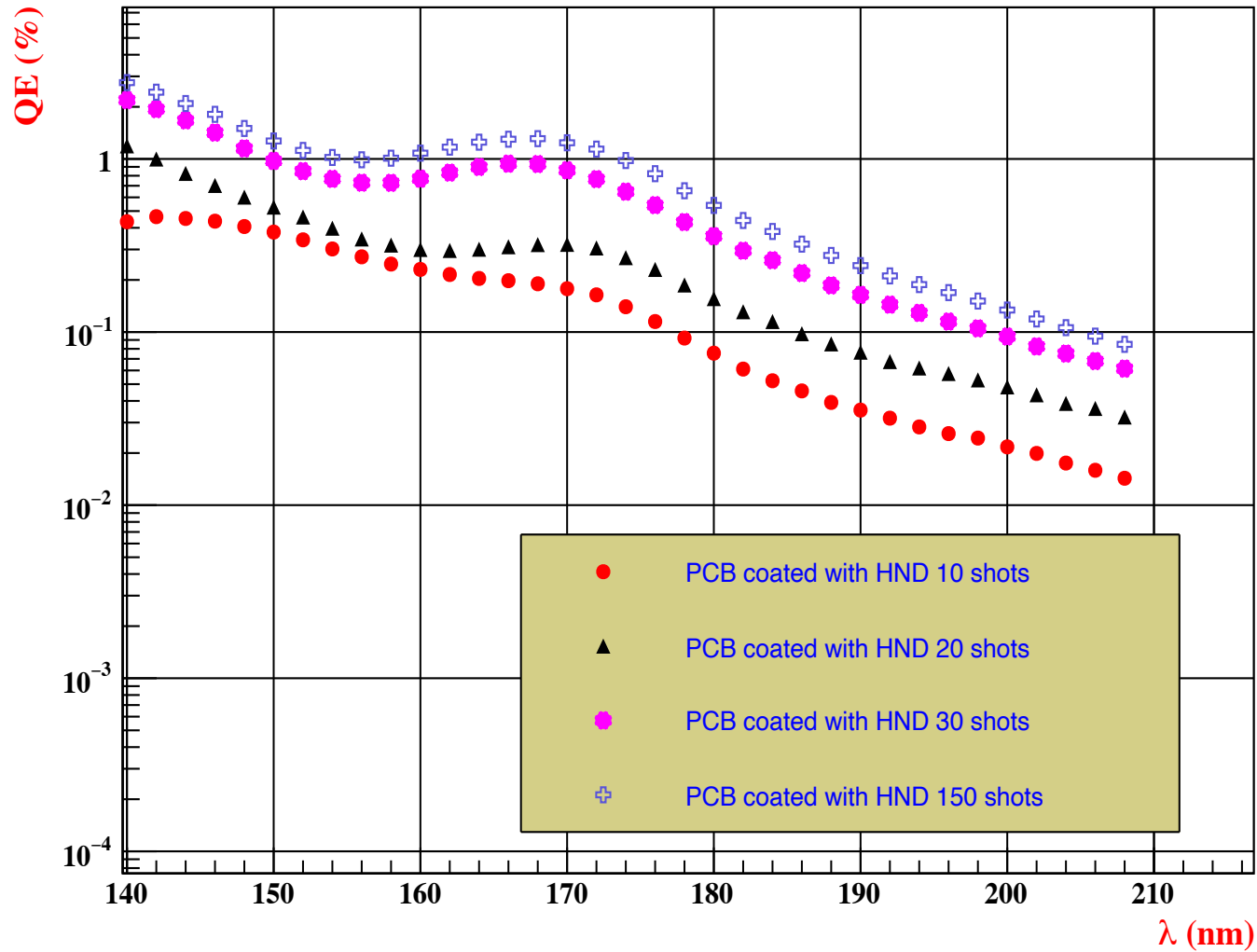


(a) Transmittance of bare and 10 shots HND coated MgF_2 and it is found to be about 40% for HND MgF_2 .



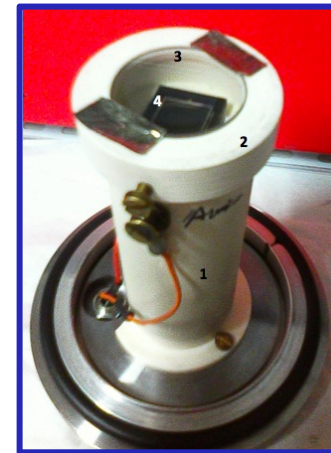
(a) Transmittance of uncoated and HND coated Cr-MgF_2 window and similar as HND coated on MgF_2 .

Quantum Efficiency of HND



Quantum Efficiency of HND has been determined by using following relation

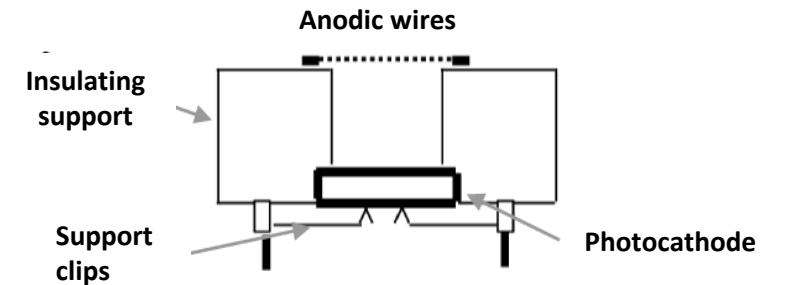
$$QE_{HND} = \frac{I_{HND}}{I_{NIST}} QE_{NIST}$$



NIST Photodiode

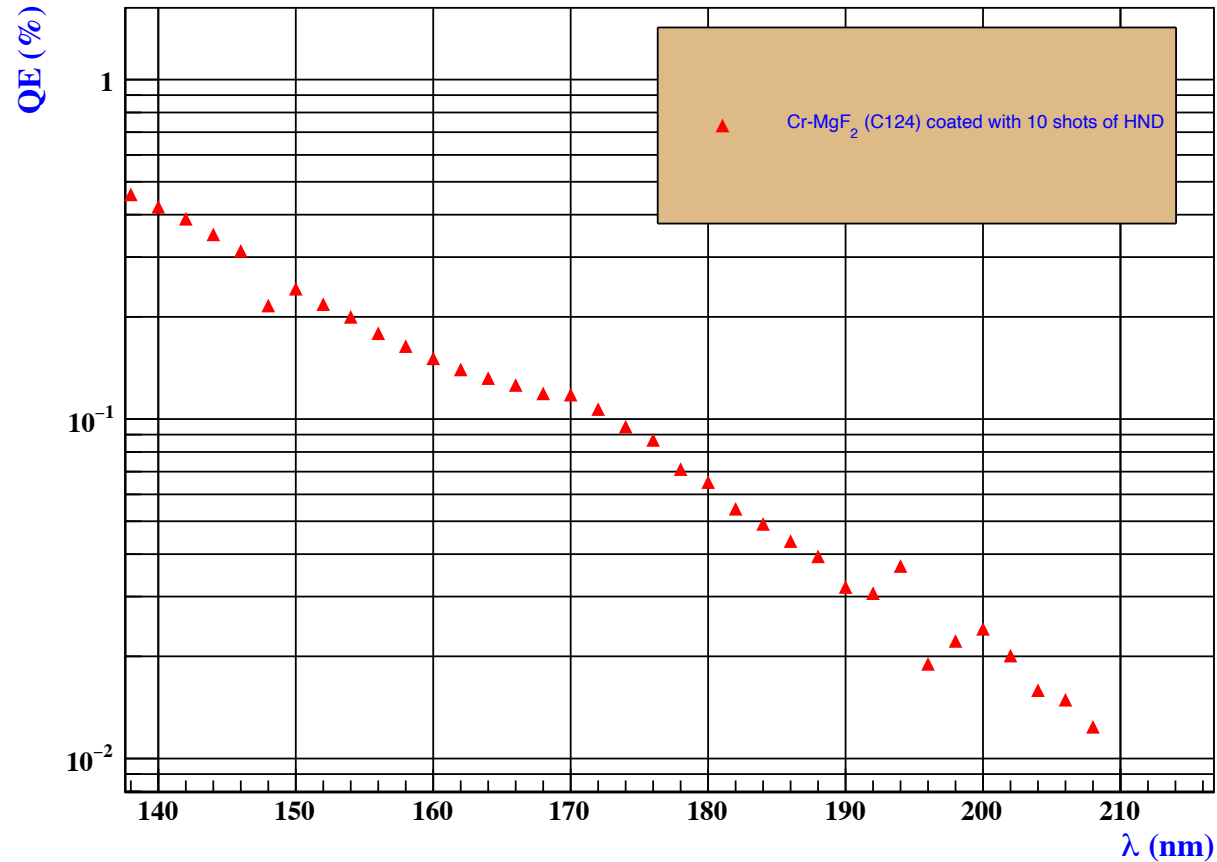


MWPC

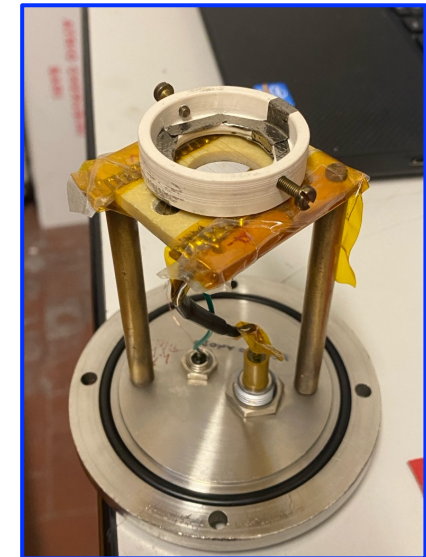
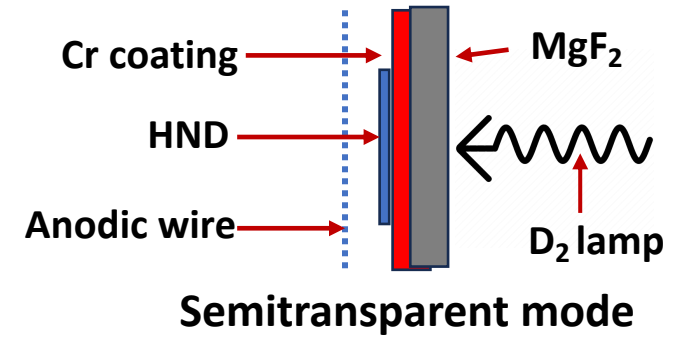


QE of HND in semitransparent mode

By coating HND on Cr-MgF₂



QE value increases for 10 shot is about ~0.4% at 140 nm wavelength.



Sample Holder

Summary

- ❑ High robustness against moisture, light irradiation, ion bombardment.
- ❑ H-ND has been applied on THGEMs and a R&D towards a detector of single photon based on hybrid (THGEM + MM) MPGD technology with H-ND photocathode has been started.
- ❑ Photoemission measurements are performed in a vacuum as in different gas mixtures.
- ❑ Transmission and QE of HND in semitransparent mode have been measured.
- ❑ A systematic study of gas, HV configuration, and detector geometry has been done.
- ❑ *Initial study suggests that; Hydrogenated Nano Diamond can be a potential candidate for future MPGD technology.*

Thank You

